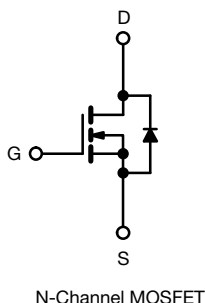
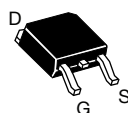


D Series Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	550	
$R_{DS(on)}$ max. (Ω) at 25 °C	$V_{GS} = 10$ V	1.5
Q_g max. (nC)	20	
Q_{gs} (nC)	3	
Q_{gd} (nC)	5	
Configuration	Single	

**DPAK
(TO-252)**



FEATURES

- Optimal design
 - Low area specific on-resistance
 - Low input capacitance (C_{iss})
 - Reduced capacitive switching losses
 - High body diode ruggedness
 - Avalanche energy rated (UIS)
- Optimal efficiency and operation
 - Low cost
 - Simple gate drive circuitry
 - Low figure-of-merit (FOM): $R_{on} \times Q_g$
 - Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Consumer electronics
 - Displays (LCD or plasma TV)
- Server and telecom power supplies
 - SMPS
- Industrial
 - Welding
 - Induction heating
 - Motor drives
- Battery chargers



RoHS
COMPLIANT
HALOGEN
FREE
Available

ORDERING INFORMATION

Package	DPAK (TO-252)
Lead (Pb)-free	SiHD5N50D-E3
Lead (Pb)-free and Halogen-free	SiHD5N50D-GE3
	SiHD5N50DT1-GE3
	SiHD5N50DT4-GE3
	SiHD5N50DT5-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	500	V
Gate-Source Voltage			V _{GS}	± 30	
Gate-Source Voltage AC (f > 1 Hz)				30	
Continuous Drain Current (T _J = 150 °C)	V _{GS} at 10 V	T _C = 25 °C	I _D	5.3	A
		T _C = 100 °C		3.4	
Pulsed Drain Current ^a			I _{DM}	10	
Linear Derating Factor				0.83	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	28.8	mJ
Maximum Power Dissipation			P _D	104	W
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +150	°C
Drain-Source Voltage Slope	T _J = 125 °C		dV/dt	24	V/ns
Reverse Diode dV/dt ^d				0.28	
Soldering Recommendations (Peak temperature) ^c	for 10 s			300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω , $I_{AS} = 5$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, starting $T_J = 25$ °C.

**THERMAL RESISTANCE RATINGS**

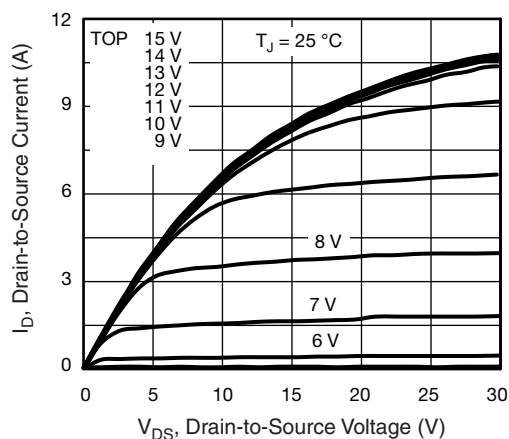
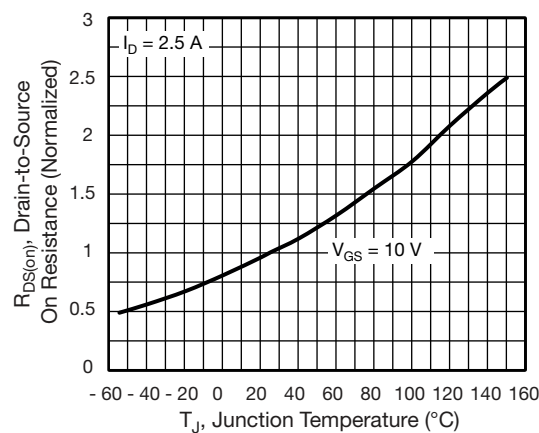
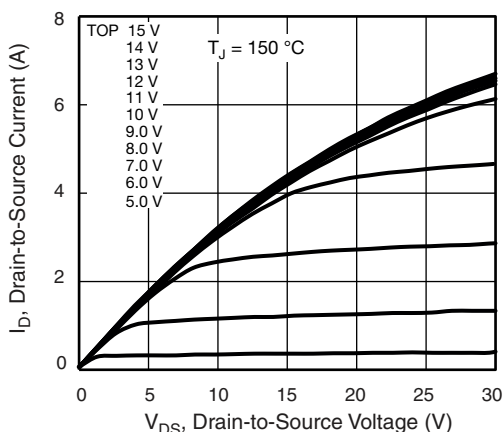
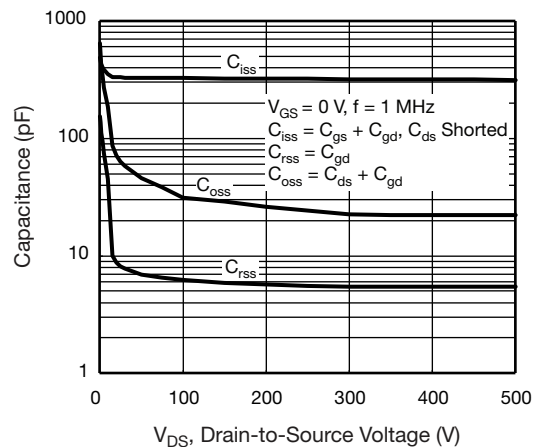
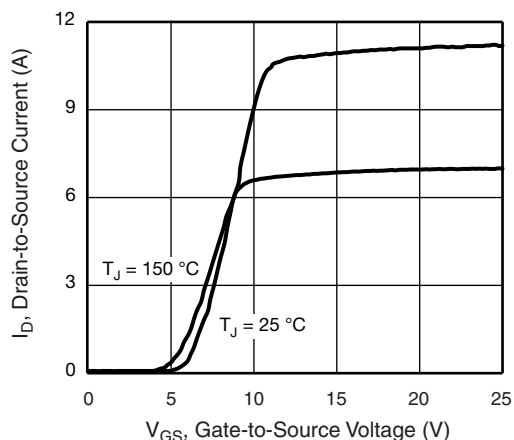
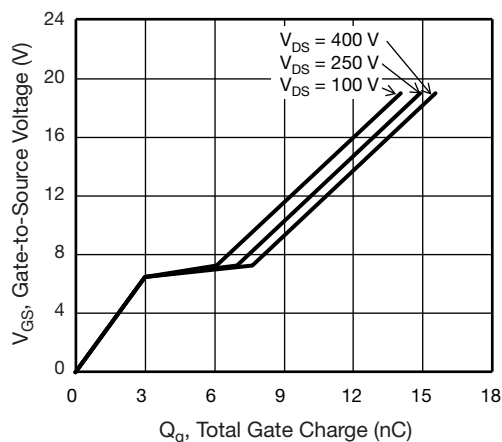
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.2	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 250\text{ }\mu\text{A}$	-	0.58	-	V/ $^{\circ}\text{C}$
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	-	5	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$	-	1.2	1.5	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 20\text{ V}$, $I_D = 2.5\text{ A}$	-	1.8	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$	-	325	-	pF
Output Capacitance	C_{oss}		-	34	-	
Reverse Transfer Capacitance	C_{rss}		-	6	-	
Effective Output Capacitance, Energy Related ^b	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 400\text{ V}$, $V_{GS} = 0\text{ V}$	-	31	-	
Effective Output Capacitance, Time Related ^c	$C_{o(tr)}$		-	41	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$, $V_{DS} = 400\text{ V}$	-	10	20	nC
Gate-Source Charge	Q_{gs}		-	3	-	
Gate-Drain Charge	Q_{gd}		-	5	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}$, $I_D = 2.5\text{ A}$, $R_g = 9.1\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	12	24	ns
Rise Time	t_r		-	11	22	
Turn-Off Delay Time	$t_{d(off)}$		-	14	28	
Fall Time	t_f		-	11	22	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	-	1.7	-	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse P - N junction diode 	-	-	5	A
Pulsed Diode Forward Current	I_{SM}		-	-	20	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 4\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S = 2.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 20\text{ V}$	-	320	-	ns
Reverse Recovery Charge	Q_{rr}		-	1.2	-	μC
Reverse Recovery Current	I_{RRM}		-	8	-	A

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature.
- b. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
- c. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

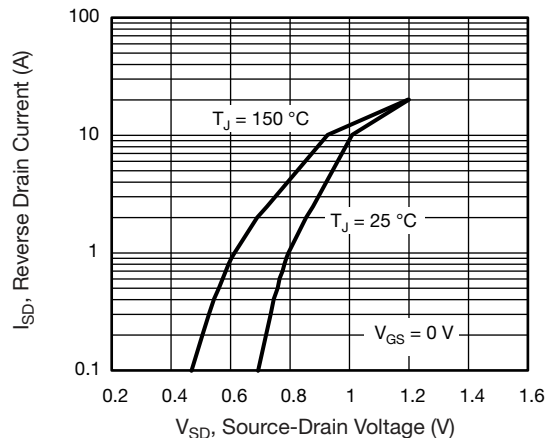
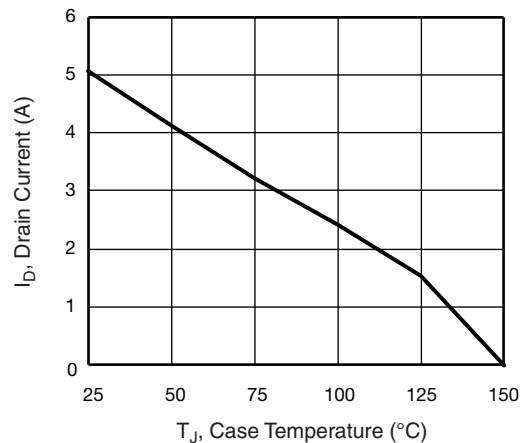
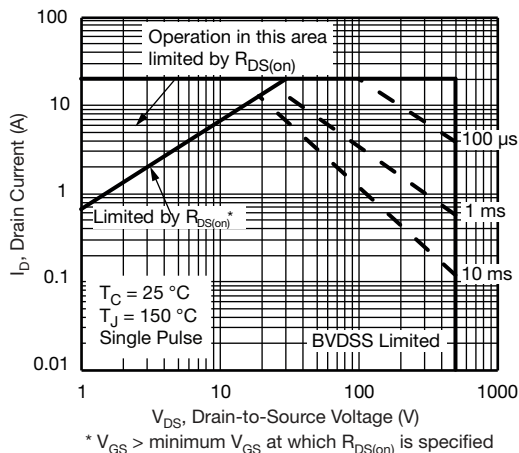
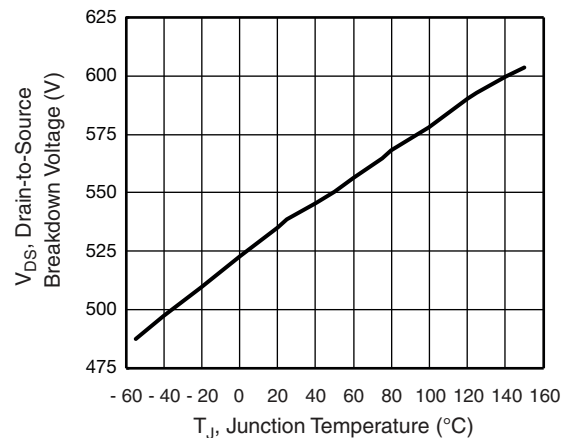
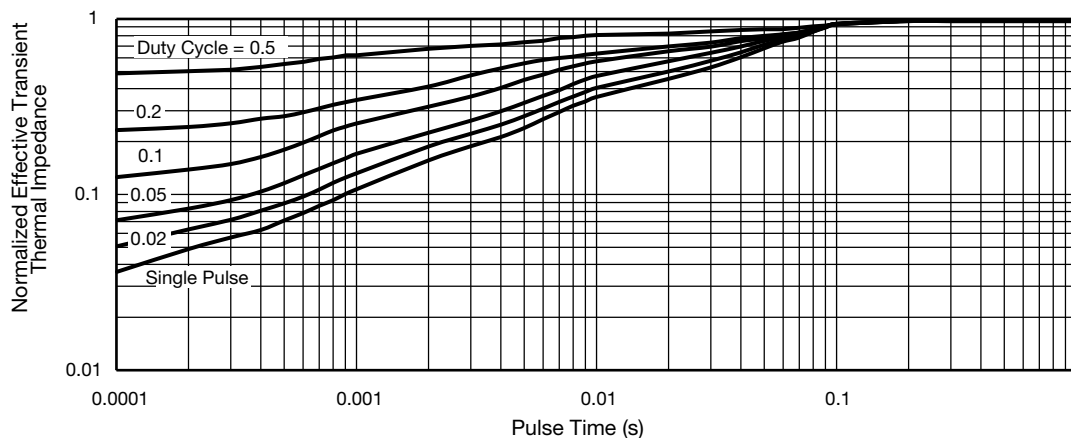
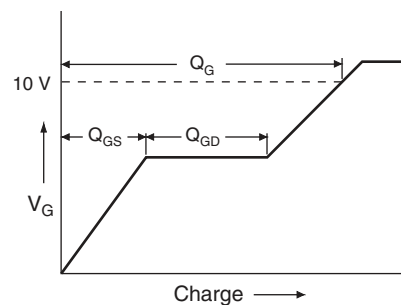
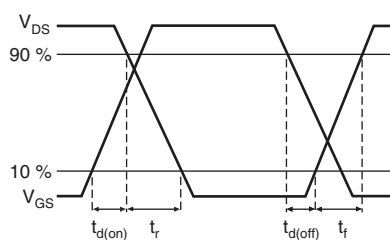
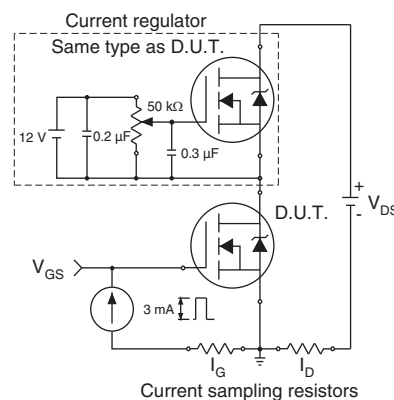
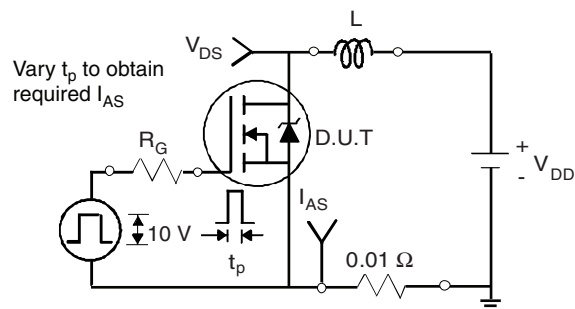
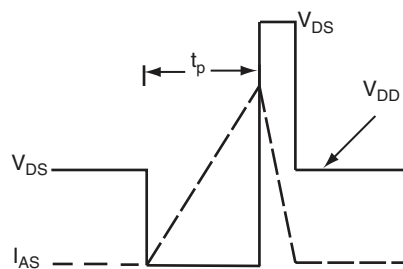

Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10 - Typical Drain-to-Source Voltage vs. Temperature

Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case


Fig. 12 - Switching Time Test Circuit

Fig. 16 - Basic Gate Charge Waveform

Fig. 13 - Switching Time Waveforms

Fig. 17 - Gate Charge Test Circuit

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 15 - Unclamped Inductive Waveforms


Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

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TO-252AA Case Outline



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347				

Notes

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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